VS-80EBU04HF4

Vishay Semiconductors

Ultrafast Soft Recovery Diode, 80 A FRED Pt®



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PRODUCT SUMMARY					
Package	PowerTab [®]				
I _{F(AV)}	80 A				
V _R	400 V				
V _F at I _F	0.92 V				
t _{rr} (typ.)	See recovery table				
T _J max.	175 °C				
Diode variation	Single die				

FEATURES

- Ultrafast recovery time
- 175 °C max. operating junction temperature
- Screw mounting only
- AEC-Q101 qualified
- PowerTab[®] package
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Cathode to anode voltage	V _R		400	V		
Continuous forward current	I _{F(AV)}	T _C = 122 °C	80			
Single pulse forward current	I _{FSM}	T _C = 25 °C	800	А		
Maximum repetitive forward current	I _{FRM}	Square wave, 20 kHz	160			
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _r	I _R = 100 μA	400	-	-	
	V _F	I _F = 80 A	-	1.1	1.3	v
Forward voltage		I _F = 80 A, T _J = 175 °C	-	0.92	1.08	
		I _F = 80 A, T _J = 125 °C		0.98	1.15	
Reverse leakage current		$V_R = V_R$ rated	-	-	50	μA
neverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	2	mA
Junction capacitance	CT	V _R = 200 V		50	-	pF
Series inductance	Ls	Measured lead to lead 5 mm from package body - 3.5 -		nH		

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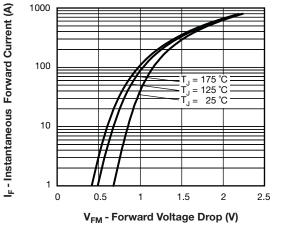
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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	50	-	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	87	-	ns
		T _J = 125 °C	I _F = 80 A V _R = 200 V dI _F /dt = 200 A/μs	-	151	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	9.3	-	A
		T _J = 125 °C		-	17.2	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	405	-	
		T _J = 125 °C		-	1300	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R _{thJC}		-	-	0.5	°C/W
Thermal resistance, junction to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-	0/00
Weight			-	-	5.02	g
weight			-	0.18	-	oz.
Mounting torque			1.2 (10)	-	2.4 (20)	N · m (lbf · in)
Marking device		Case style PowerTab [®]		80EB	U04H	

VS-80EBU04HF4

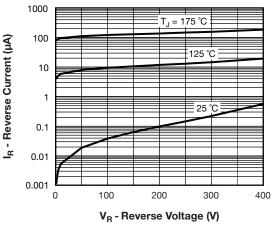
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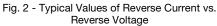


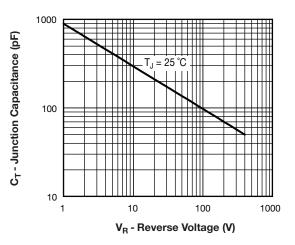
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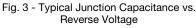
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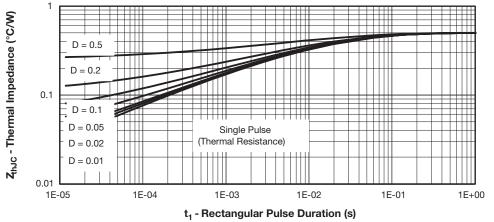










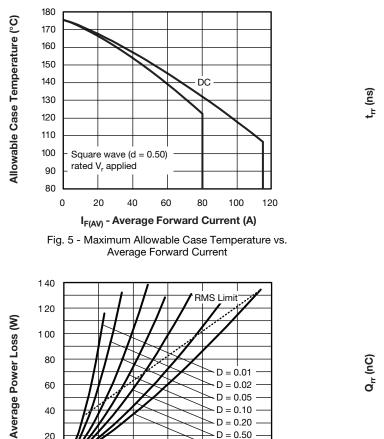




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D = 0.01

D = 0.02 D = 0.05

D = 0.10

D = 0.20 D = 0.50

100

120

-DC

80

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ISHAY

60

40

20

0

0

20

40

60

I_{F(AV)} - Average Forward Current (A)

Fig. 6 - Forward Power Loss Characteristics

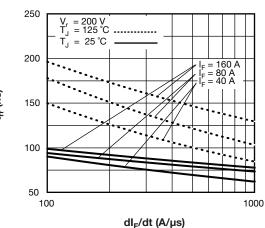


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

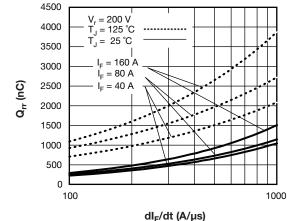


Fig. 8 - Typical Stored Charge vs. dl_F/dt

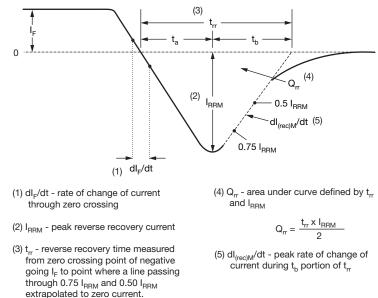


Fig. 9 - Reverse Recovery Waveform and Definitions

	→	
	Q _{rr} (4) I _{RRM} 0.5 I _{RRM} dI _{(rec)M} /dt (5) 0.75 I _{RRM}	
 dI_F/dt - rate of change of current through zero crossing 	(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}	
(2) I _{RRM} - peak reverse recovery current	$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$	
(3) t _{rr} - reverse recovery time measured from zero crossing point of negative	(5) dl _{(rec)M} /dt - peak rate of change of	

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ORDERING INFORMATION TABLE

Device code	VS-	80	Е	В	U	04	н	F4
		2	3	4	5	6	7	8
	1 -	· Visł	nay Sem	niconduc	ctors pro	oduct		
	2 -	Cur	rent rati	ng (80 =	80 A)			
	3 -	Sing	gle diode	е				
	4 -	Pow	/erTab [®]	1				
	5 -	Ultra	afast reo	covery				
	6 -	· Volt	age rati	ng (04 =	400 V)			
	7 -	- H=	AEC-Q	101 qua	lified			
	8 -	- Env	ironmer	ntal digit	:			
		F4 :	= RoHS	-complia	ant and	totally le	ad (Pb)	-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	REFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-80EBU04HF4	25	375	Antistatic plastic tube				

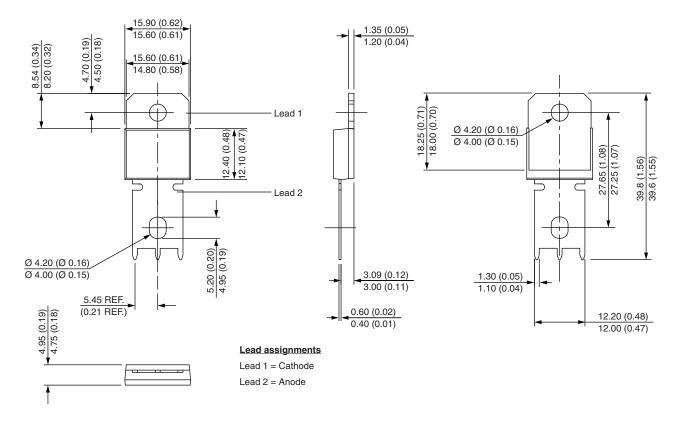
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95240				
Part marking information	www.vishay.com/doc?95467				
Application note	www.vishay.com/doc?95179				



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PowerTab[®]

DIMENSIONS in millimeters (inches)





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